33082R003



PATENT **EXPEDITED PROCESSING**

AFTER FINAL STATUS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants

NANBU, et al.

Serial No.

09/233,073

Examiner: Vinh, L.

Filed

January 19, 1999

Group Art Unit: 1765

For

METHOD OF ETCHING

PETITION UNDER 37 C.F.R. §1.97(d)

Assistant Commissioner for Patents Washington, D.C. 20231

Sir:

In accordance with 37 C.F.R. §1.97(d), Applicants respectfully request entry and consideration of the attached Information Disclosure Statement. Applicants attach a Certification Under 37 C.F.R. §1.97(e)(2) hereto. Also attached hereto is a check in the amount of \$130 for the associated Petition fee. Please charge any additional fees or credit any overpayment to Deposit Account No. 02-4300.

Respectfully submitted,

SMITH, GAMBRELL & RUSSELL, LLP The Beveridge, Degrandi, Weilacher & Young Intellectual Property Group

By:

Dennis C. Rodgers, Reg. No. 32,936

1850 M Street, N.W., Suite 800

Washington, D.C. 20036 Telephone: (202) 659-2811 Facsimile: (202) 659-1462

July 26, 2000

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CERTIFICATION UNDER 37 C.F.R. § 1.97(e)(2)

In accordance with 37 C.F.R. § 1.97(e)(2), Applicants certify that no item of information contained in the accompanying information disclosure statement was cited in a communication from a foreign patent office in counterpart foreign application, and to the knowledge of the person signing the statement after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in § 1.56(c) more than three months prior to the filing of the information disclosure statement.

Respectfully submitted,

SMITH, GAMBRELL & RUSSELL, LLP BEVERIDGE, DEGRANDI, WEILACHER & YOUNG INTELLECTUAL PROPERTY GROUP

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INFORMATION DISCLOSURE STATEMENT WITH PETITION UNDER 37 C.F.R. 1.97(d)

Assistant Commissioner for Patents Washington, D.C. 20231

Sir:

This Information Disclosure Statement is further to the Amendment After Final filed on July 24,

2000 for the above-identified case and is accompanied by the following documents:

- 1) PTO 1449 form citing two references
- 2) Petition Under 37 C.F.R. 1.97(d)
- 3) Certification Under 37 C.F.R. 1.97(e)(2)
- 4) Copy of each article referenced in (1) above
- 5) Check for \$130.00

Entry and consideration of the references accompanying this Information Disclosure Statement

(and also earlier provided with the Amendment After Final) is respectfully requested.

Respectfully submitted,

SMITH, GAMBRELL & RUSSELL, LLP BEVERIDGE, DEGRANDI, WEILACHER & YOUNG

INTELLECTUAL PROPERTY GROUP

By:

Dennis C. Rodgers, Reg. No. 32,936 1850 M Street, NW - Suite 800 Washington, DC 20036

TEL: (202) 659-2811

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U.S. Patent Documents									
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OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)									
LV	AQ	Two-Dimensional Modeling of High Plasma Density Inductively Coupled Sources for Materials Processing, J. Vac Sci. Technol. B 12(1), Jan/Feb 1994, pp. 461-476							
LV	AR	"Hybrid Plasma Equipment Model Inductively Coupled Plasma Reactive Ion Etching Reactors" Computational Optical and Discharge Physics, University of Illinois College of Engineering, pp. 1-4 (date not designated)							
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